

Patent  
10/770,045

**IN THE SPECIFICATION:**

Please amend the Title to read:

Power Semiconductor Device Having a Voltage Sustaining Region That Includes Terraced Trench with Continuous Doped Columns Formed in an Epitaxial Layer ~~With a Single Ion Implantation Step~~

Please amend paragraph [0001] of the specification as follows:

[0001] This application is a divisional application of co-pending U.S. Patent Application 10/103,674, filed March 21, 2002, now US Patent 6,686,244, entitled "Power Semiconductor Device Having A Voltage Sustaining Region That Includes Doped Columns Formed With A Single Ion Implantation Step."